

Journal of Nuclear Materials 249 (1997) 128-132



On the origin of the F⁺ centre radioluminescence in sapphire

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Received 16 June 1997: accepted 1 July 1997

Abstract

Electron irradiation of sapphire produces primarily F centres, in marked contrast with neutron and ion irradiations where both F and F^+ centres are produced. However, radioluminescence studies during electron irradiation indicate bands associated with both F and F^+ centres. These emission bands show a complex dependence on dose rate and temperature. A systematic study of the radioluminescence spectra as a function of these two parameters together with optical absorption measurements indicate that the ionization of F centres is the cause of the F^+ centre radioluminescence. A model describing the way the F^+ emission occurs is proposed and compared with the results obtained. © 1997 Elsevier Science B.V.

1. Introduction

For many years α -Al₂O₃ has been considered a material of technological interest for diverse applications such as dielectric substrates for SOS structures, solid state lasers, UV windows, radiation dosimeters and, more recently, fusion energy devices. As a consequence of this interest numerous papers have been published concerning the defects in α -Al₂O₃. In these studies undoubtedly the point defects which have received most attention are the so-called F and F⁺ centres (oxygen vacancies with two and one trapped electron, respectively).

Oxygen vacancies in α -Al₂O₃ result from either thermochemical reduction during vacuum heat treatment [1] or from lattice displacement events during particle irradiation [2–9]. Optical absorption measurements have shown that when sapphire (single crystal α -Al₂O₃) is irradiated with neutrons, protons, or other ions, both F and F⁺ centres are produced [2–8]. However, when sapphire is irradiated with electrons essentially only F centres are produced, as evidenced by the single absorption band at 6.03 eV [2,3,9]. In apparent contradiction with the optical absorption results, radioluminescence measurements for electron irradiated sapphire show luminescence bands at 3.0 and 3.8 eV corresponding to both F and F⁺ centres [9–11]. In view of the fact that radioluminescence measurements are now

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being employed as a tool to study oxygen vacancy production in sapphire it is essential that these differences be understood [10-16].

The aim of this paper is to clarify the origin of the F^+ centre radioluminescence in electron irradiated sapphire and to reconcile the above apparent contradiction. To achieve this objective a systematic study of the F and F^+ radioluminescence bands as a function of dose rate and temperature has been made. A model describing how the F^+ radioluminescence occurs is proposed and then used to explain the results obtained.

2. Experimental procedure

The work reported here has been performed in a chamber mounted in the beam line of a 2 MeV Van de Graaff accelerator, in which a Union Carbide UV grade sapphire sample has been irradiated with 1.8 MeV electrons. The sample, approximately $5 \times 5 \times 1 \text{ mm}^3$ in size, was placed sandwich-like between the faces of a double oven and irradiated edge-on through a $3 \times 1 \text{ mm}^2$ collimator on to one of the $5 \times 1 \text{ mm}^2$ faces. Two $3 \times 1 \text{ mm}^2$ windows cut in the oven enable in situ measurements of optical absorption and radioluminescence to be made perpendicular to the irradiated face. The sample may be heated from 15 to 650°C and maintained at any temperature to within 1°C.

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The sample was initially irradiated at 50°C, 3 μ A cm⁻² for 14 h to produce oxygen vacancies. During irradiation, radioluminescence spectra were taken to monitor the increase in the oxygen vacancy concentration. After 14 h the change with irradiation time in the radioluminescence spectra was slow enough to enable a study to be carried out as a function of dose rate (beam current) and irradiation temperature. In this study radioluminescence spectra at beam currents of between 0.025 and 10 μ A cm⁻² for temperatures between 50 and 200°C were taken. Each recorded spectrum took approximately 3 min and the total integrated dose was observed to have no measurable effect on the reference spectrum recorded following the initial 14 h of irradiation, as evidenced by a further reference spectrum taken at the end of the experiment. In addition, optical absorption spectra were recorded before and after irradiation.

3. Results

Fig. 1 shows radioluminescence spectra for the initial part of the experiment at 50°C, 3 μ A cm⁻² for different irradiation times in which one observes the growth of bands at about 410 (3.0 eV) and 329 nm (3.8 eV) corresponding to F and F⁺ centres, respectively [17], together with a decrease in the Ga^{3+} emission at 250 nm [18]. Following 14 h of irradiation very little further change was observed for these bands. In Figs. 2 and 3 radioluminescence spectra at 50°C for 0.25 and 10 µA cm⁻² following the initial 14 h irradiation are given. One observes that the relative amounts of F and F⁺ emission depend on the beam current (dose rate). This dependence is more clearly seen in Fig. 4 where radioluminescence spectra for three different dose rates are presented, normalised to unit dose rate. We observed that the normalised F⁺ emission increases and the normalised F emission decreases on increasing the dose rate. Exactly the reverse behaviour was



Fig. 1. Radioluminescence spectra for sapphire irradiated at 50°C, 3 μ A cm⁻² after irradiation for; 1 min (1), 30 min (2), 110 min (3) and 240 min (4).



Fig. 2. Radioluminescence spectrum taken at 50°C and 0.25 μ A cm⁻² following 14 h of irradiation at 50°C, 3 μ A cm⁻². The F radioluminescence band is much larger than the F⁺ band.



Fig. 3. Radioluminescence spectrum taken at 50°C and 10 μ A cm⁻² following 14 h of irradiation at 50°C, 3 μ A cm⁻². The F radioluminescence band is much smaller than the F⁺ band.



Fig. 4. Radioluminescence spectra normalized to dose rate (intensity divided by beam current), taken at 50°C for 0.5 (1), 2.5 (2) and 10 μ A cm⁻² (3) after 14 h irradiation at 50°C and 3 μ A cm⁻².



Fig. 5. Optical absorption spectrum for sapphire after 14 h irradiation at 50°C and 3 μ A cm⁻². Only the F centre band at about 205 nm is visible.

observed on decreasing the dose rate. Very similar results were obtained for irradiations at 100, 150 and 200°C. These results clearly indicate that the F emission intensity depends sub-linearly on dose rate while the F^+ intensity has a superlinear dependence.

The optical absorption spectrum taken at the end of the experiment can be seen in Fig. 5. A band at 206 nm due to F centres is clearly observed [2] corresponding to a density of approximately 10^{16} centres/cm³. But there is no indication above the background of optical absorption bands at about 229 or 256 nm associated with F⁺ centres [2,4].

4. Discussion

The optical absorption measurements (Fig. 5) show that essentially only F centres are produced when sapphire is irradiated with electrons, in agreement with previous results [2,3,10]. However, as may be seen in Figs. 1-4, both F and F⁺ radioluminescence bands are observed during irradiation. It is clear from Figs. 2-4 that these two emission bands show a complex dependence on dose rate, with the intensity of the F⁺ emission increasing super-linearly with dose rate while the F centre emission increases sub-linearly with dose rate. This behaviour, together with the reversibility on decreasing dose rate and the absence of F⁺ centres in the optical absorption, suggests that the origin of the F⁺ centre radioluminescence is related to the ionization of F centres. One is at first tempted to envisage the F⁺ radioluminescence as a simple three-step process in which; firstly one F centre is ionised becoming an F^+ centre, then this F⁺ centre is excited and, finally, it de-excites emitting a 3.8 eV photon. However such a process is questionable as it requires two consecutive energy depositions at the oxygen vacancy to occur on a time scale less than the time between vacancy ionization and localization at the defect of an electron from the conduction band, which is known to be $< 10^{-12}$ s [19].

The above problem may be overcome if we take into account the mechanism for energy absorption by the lattice and the way F^+ to F centre conversion occurs. In insulating materials radiation is mainly absorbed by the excitation of electrons from the valence band into the conduction band producing electrons and holes [20]. These either recombine or migrate through the lattice where they interact with defects. The interaction of a hole with an F centre produces an F^+ centre. This F^+ centre rapidly (< 10⁻¹² s) traps an electron from the conduction band to form an F^+ centre (excited F centre). The F^+ centre radiolumines-cence).

However the F^* centre has a lifetime of the order of tens of milliseconds related to the strongly forbidden triplet to singlet transition [9,17]. This long lifetime will increase the probability that a further hole may recombine at the F^* centre before the centre de-excites. Such an interaction between a hole and the ground state electron leaves an excited F^+ centre (F^{+*}). In this case the transition to the ground state is allowed and de-excitation occurs rapidly with a lifetime of less than 8 ns, emitting a 3.82 eV photon (F^+ centre radioluminescence) [5]. We can now use this model to obtain a relationship between the intensities of the radioluminescence bands associated with F and F^+ centres.

The processes involved are

(1) $F + h/e \rightarrow F^*$: Excitation of the F centre by electron and hole capture;

(2) $F^* \rightarrow F + h\nu_F$: De-excitation of the F^* giving F luminescence:

(3) $F^* + h \rightarrow F^{+*}$: Ionization of the F^* by hole capture giving F^{+*} ;

(4) $F^{+*} \rightarrow F^{+} + h\nu_{F^{+}}$: De-excitation of the F^{+*} giving F^{+} luminescence;

(5) $F^+ + e \rightarrow F^*$: Reconversion of F^+ to F^* by electron capture.

Fig. 6 gives a sequential flow diagram for these processes. We can see that the F⁺ radioluminescence RL_{F^+} (steps 3 and 4) comes from the ionization of the F^{*} and is directly proportional to the number of F^{+*} and as all the F^{+*} de-excite to give F⁺ we can write

$$\mathsf{RL}_{\mathsf{F}^+} = AN_{\mathsf{F}^+},\tag{1}$$

where A is a constant and N_{F^+} is the F^+ concentration.

In contrast, the F radioluminescence RL_F (step 2) which comes from the de-excitation of the F^{*} is not directly proportional to the number of F^{*} because these can either de-excite (step 2) or convert to F^{+*} (step 3). In this case RL_F is proportional to the number of F^{*} and inversely proportional to the probability of F^{*} to F^{+*} conversion, which is proportional to the hole production rate, i.e., the dose rate Φ . Hence we have

$$RL_{F} = BN_{F} \cdot 1/\Phi, \qquad (2)$$

where B is a constant and N_{F^*} is the F^{*} concentration.



Fig. 6. Flow diagram for the F and F⁺ luminescence processes.

Once steady state conditions are reached, which also requires that the oxygen vacancy concentration is constant or varies only very slowly with time, the numbers of F, F^* , F^+ , and F^{+*} centres are constant. Under these conditions the number of F^* centres converted to F^{+*} centres per unit time (step 3) has to be equal to the number of F^{+*} centres reconverting via F^+ to F^* centres (steps 4 and 5). The former is proportional to the F^* centre concentration (N_{F^*}) and ionizing dose rate Φ , while the latter is proportional to the F^+ centre concentration (N_{F^*}) and the concentration of the unpaired electrons promoted to the conduction band during the conversion of F to F^+ , which is also equal to N_{F^*} . Thus the steady state rate equation

$$N_{\rm F} \cdot \Phi = C(N_{\rm F^+})^2, \tag{3}$$

where C is a constant.



Fig. 7. Log-log plot of the height of the F^+ radioluminescence band versus the product of the dose rate (beam current) and the square root of the height of the F radioluminescence band at 50°C, for beam currents from 0.025 to 10 μ A cm⁻². The straight line fit is of slope 1.



Fig. 8. Plot of the height of the F^+ radioluminescence band versus the product of the dose rate and the square root of the height of the F radioluminescence band at 50, 100, 150 and 200°C, for beam currents from 0.025 to 10 μ A cm⁻².

If we now substitute for $N_{\rm F}$. and $N_{\rm F^+}$ from Eqs. (1) and (2) we obtain

 $RL_{F^{+}} = D\Phi \sqrt{RL_{F}}$ where D = A/l(BC), a constant. (4)

Hence we see from Eq. (4) that if the above model is essentially correct, a plot of the height of the F^+ radioluminescence band versus the product of the dose rate and the square root of the height of the F radioluminescence band should be a straight line. As may be seen in Figs. 7 and 8 this prediction is fulfilled over a wide dose rate range, and for various temperatures. The effect of the temperature on the slope (Fig. 8) may be due to a differential decrease in the F and F⁺ band heights on increasing temperature [10], or a possible decrease in the F^{*} lifetime with increasing temperature [21].

It is therefore clear that the F^+ radioluminescence observed during the electron irradiation of sapphire is not a measure of stable F^+ centres, but is a consequence of the long lifetime of the F^+ centre and its ionization to give F^+ centres. Furthermore, it is important to notice that the experimentally observed F radioluminescence intensity also cannot be used as an indication of the F centre concentration.

5. Conclusions

The results presented here show that F and F^+ radioluminescence depend in a complex way on the ionizing dose rate. The observation of F^+ luminescence does not indicate the presence of stable F^+ centres, and the F luminescence cannot be used as a direct indication of the F centre concentration. A model describing the way F and F^+ centre radioluminescence occurs has been developed. This model predicts a complex dependence with dose rate of the F and F^+ centre radioluminescence, which has been experimentally observed.

Acknowledgements

The authors are indebted to Mr J. Montesinos and Mr E. Sanchez-Cabezudo for their valuable help in these experiments.

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